

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

**TC74LCX00F, TC74LCX00FN, TC74LCX00FT****LOW-VOLTAGE QUAD 2-INPUT NAND GATE  
WITH 5V TOLERANT INPUTS AND OUTPUTS**

The TC74LCX00 is a high performance CMOS 2-INPUT NAND GATE. Designed for use in 3.3 Volt systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

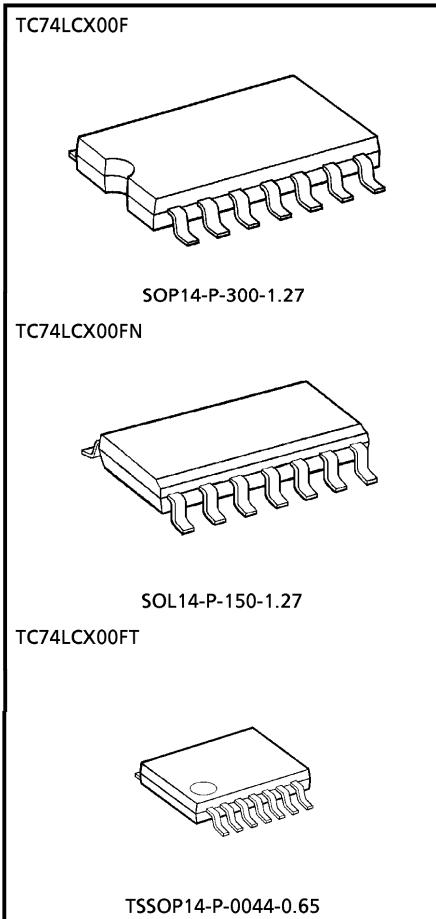
The device is designed for low-voltage (3.3V) V<sub>CC</sub> applications, but it could be used to interface to 5V supply environment for inputs.

All inputs are equipped with protection circuits against static discharge.

**FEATURES**

- Low voltage operation : V<sub>CC</sub> = 2.0~3.6V
- High speed operation : t<sub>pd</sub> = 5.2ns (Max.) at V<sub>CC</sub> = 3.0~3.6V
- Output current : |I<sub>OH</sub>| / |I<sub>OL</sub>| = 24mA (Min.) at V<sub>CC</sub> = 3.0V
- Latch-up performance : ±500mA
- Available in JEDEC SOP, EIAJ SOP and TSSOP
- Power down protection is provided on all inputs and outputs.
- Pin and function compatible with the 74 series (74AC/VHC/HC/F/ALS/LS etc.) 00 type.

(Note) The JEDEC SOP (FN) is not available in Japan.

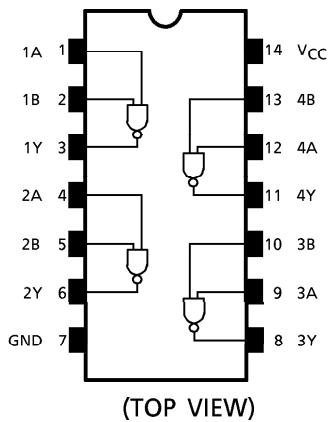


**Weight**  
 SOP14-P-300-1.27 : 0.18g (Typ.)  
 SOL14-P-150-1.27 : 0.12g (Typ.)  
 TSSOP14-P-0044-0.65 : 0.06g (Typ.)

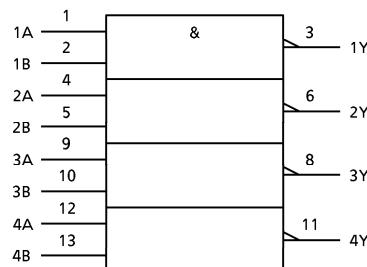
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## PIN CONNECTION



## IEC LOGIC SYMBOL



## TRUTH TABLE

INPUTS		OUTPUTS
A	B	Y
L	L	H
L	H	H
H	L	H
H	H	L

## MAXIMUM RATINGS

PARAMETER	SYMBOL	RATING	UNIT
Power Supply Voltage	V <sub>CC</sub>	-0.5~7.0	V
DC Input Voltage	V <sub>IN</sub>	-0.5~7.0	V
DC Output Voltage	V <sub>OUT</sub>	-0.5~7.0 (Note 1)	V
		-0.5~V <sub>CC</sub> + 0.5 (Note 2)	
Input Diode Current	I <sub>IK</sub>	-50	mA
Output Diode Current	I <sub>OK</sub>	± 50 (Note 3)	mA
DC Output Current	I <sub>OUT</sub>	± 50	mA
Power Dissipation	P <sub>D</sub>	180	mW
DC V <sub>CC</sub> / Ground Current	I <sub>CC</sub> / I <sub>GND</sub>	± 100	mA
Storage Temperature	T <sub>stg</sub>	-65~150	°C

(Note 1) V<sub>CC</sub> = 0V(Note 2) High or Low State. I<sub>OUT</sub> absolute maximum rating must be observed.(Note 3) V<sub>OUT</sub> < GND, V<sub>OUT</sub> > V<sub>CC</sub>

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## RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage	$V_{CC}$	2.0~3.6	V
		1.5~3.6 (Note 4)	
Input Voltage	$V_{IN}$	0~5.5	V
Output Voltage	$V_{OUT}$	0~5.5 (Note 5)	V
		0~ $V_{CC}$ (Note 6)	
Output Current	$I_{OH}/I_{OL}$	$\pm 24$ (Note 7)	mA
		$\pm 12$ (Note 8)	
Operating Temperature	$T_{opr}$	-40~85	°C
Input Rise And Fall Time	$dt/dv$	0~10 (Note 9)	ns/V

(Note 4) Data Retention Only

(Note 5)  $V_{CC} = 0V$ 

(Note 6) High or Low State

(Note 7)  $V_{CC} = 3.0~3.6V$ (Note 8)  $V_{CC} = 2.7~3.0V$ (Note 9)  $V_{IN} = 0.8~2.0V, V_{CC} = 3.0V$ 

## ELECTRICAL CHARACTERISTICS

DC CHARACTERISTICS ( $T_a = -40~85^\circ C$ )

PARAMETER	SYMBOL	TEST CONDITION	$V_{CC}$ (V)	MIN.	MAX.	UNIT	
			2.7~3.6				
Input Voltage	"H" Level	$V_{IH}$	2.7~3.6	2.0	—	V	
	"L" Level	$V_{IL}$		—	0.8	V	
Output Voltage	"H" Level	$V_{OH}$	$V_{IN} = V_{IH}$ or $V_{IL}$	$I_{OH} = -100\mu A$	2.7~3.6	$V_{CC} - 0.2$	V
				$I_{OH} = -12mA$	2.7	2.2	
				$I_{OH} = -18mA$	3.0	2.4	
				$I_{OH} = -24mA$	3.0	2.2	
	"L" Level	$V_{OL}$	$V_{IN} = V_{IH}$	$I_{OL} = 100\mu A$	2.7~3.6	—	V
				$I_{OL} = 12mA$	2.7	—	
				$I_{OL} = 16mA$	3.0	—	
				$I_{OL} = 24mA$	3.0	—	
Input Leakage Current	$I_{IN}$	$V_{IN} = 0~5.5V$	2.7~3.6	—	$\pm 5.0$	$\mu A$	
Power Off Leakage Current	$I_{OFF}$	$V_{IN}/V_{OUT} = 5.5V$	0	—	10.0	$\mu A$	
Quiescent Supply Current	$I_{CC}$	$V_{IN} = V_{CC}$ or GND	2.7~3.6	—	10.0	$\mu A$	
		$V_{IN}/V_{OUT} = 3.6~5.5V$	2.7~3.6	—	$\pm 10.0$		
Increase In $I_{CC}$ Per Input	$\Delta I_{CC}$	$V_{IH} = V_{CC} - 0.6V$	2.7~3.6	—	500	$\mu A$	

AC CHARACTERISTICS ( $T_a = -40\sim85^\circ C$ )

PARAMETER	SYMBOL	TEST CONDITION	$V_{CC}$ (V)	MIN.	MAX.	UNIT
Propagation Delay Time	$t_{PLH}$	(Fig.1, 2)	2.7	—	6.0	ns
	$t_{PLH}$		$3.3 \pm 0.3$	1.5	5.2	
Output To Output Skew	$t_{osLH}$	(Note 10)	2.7	—	—	ns
	$t_{osHL}$		$3.3 \pm 0.3$	—	1.0	

(Note 10) Parameter guaranteed by design.

$$(t_{osLH} = |t_{PLHm} - t_{PLHn}|, t_{osHL} = |t_{PLHm} - t_{PLHn}|)$$

DYNAMIC SWITCHING CHARACTERISTICS ( $T_a = 25^\circ C$ , Input  $t_r = t_f = 2.5\text{ns}$ ,  $C_L = 50\text{pF}$ ,  $R_L = 500\Omega$ )

PARAMETER	SYMBOL	TEST CONDITION	$V_{CC}$ (V)	TYP	UNIT
Quiet Output Maximum Dynamic $V_{OL}$	$V_{OLP}$	$V_{IH} = 3.3\text{V}$ , $V_{IL} = 0\text{V}$	3.3	0.8	V
Quiet Output Minimum Dynamic $V_{OL}$	$ V_{OLV} $	$V_{IH} = 3.3\text{V}$ , $V_{IL} = 0\text{V}$	3.3	0.8	V

CAPACITIVE CHARACTERISTICS ( $T_a = 25^\circ C$ )

PARAMETER	SYMBOL	TEST CONDITION	$V_{CC}$ (V)	TYP.	UNIT	
Input Capacitance	$C_{IN}$	—	3.3	7	pF	
	$C_{OUT}$		0	8	pF	
Power Dissipation Capacitance	$C_{PD}$	$f_{IN} = 10\text{MHz}$	(Note 11)	3.3	25	pF

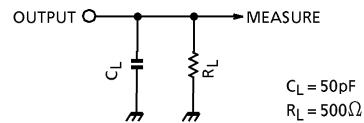
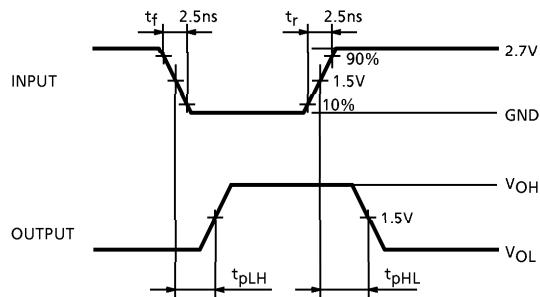
(Note 11)  $C_{PD}$  is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC(\text{opr.})} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/4 \text{ (Per gate)}$$

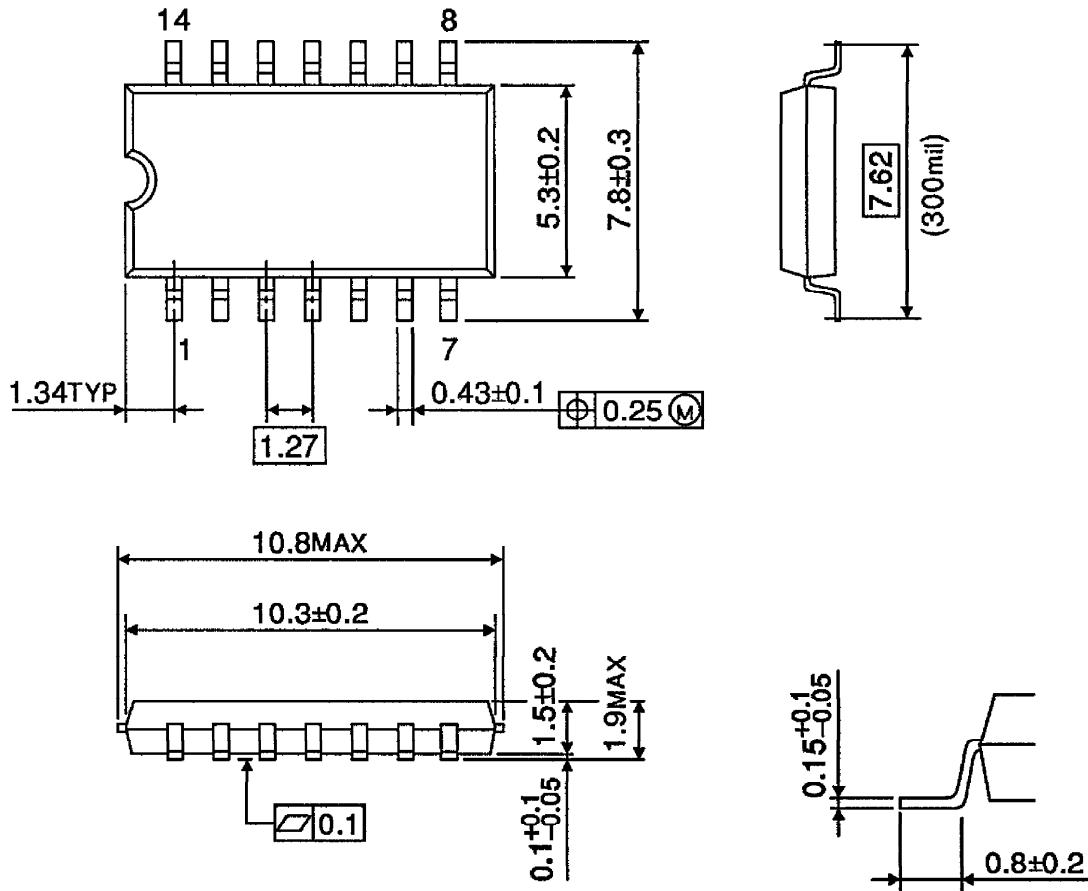
**TEST CIRCUIT**

Fig.1

**AC WAVEFORM**Fig.2  $t_{pLH}$ ,  $t_{pHL}$ 

**OUTLINE DRAWING**  
SOP14-P-300-1.27

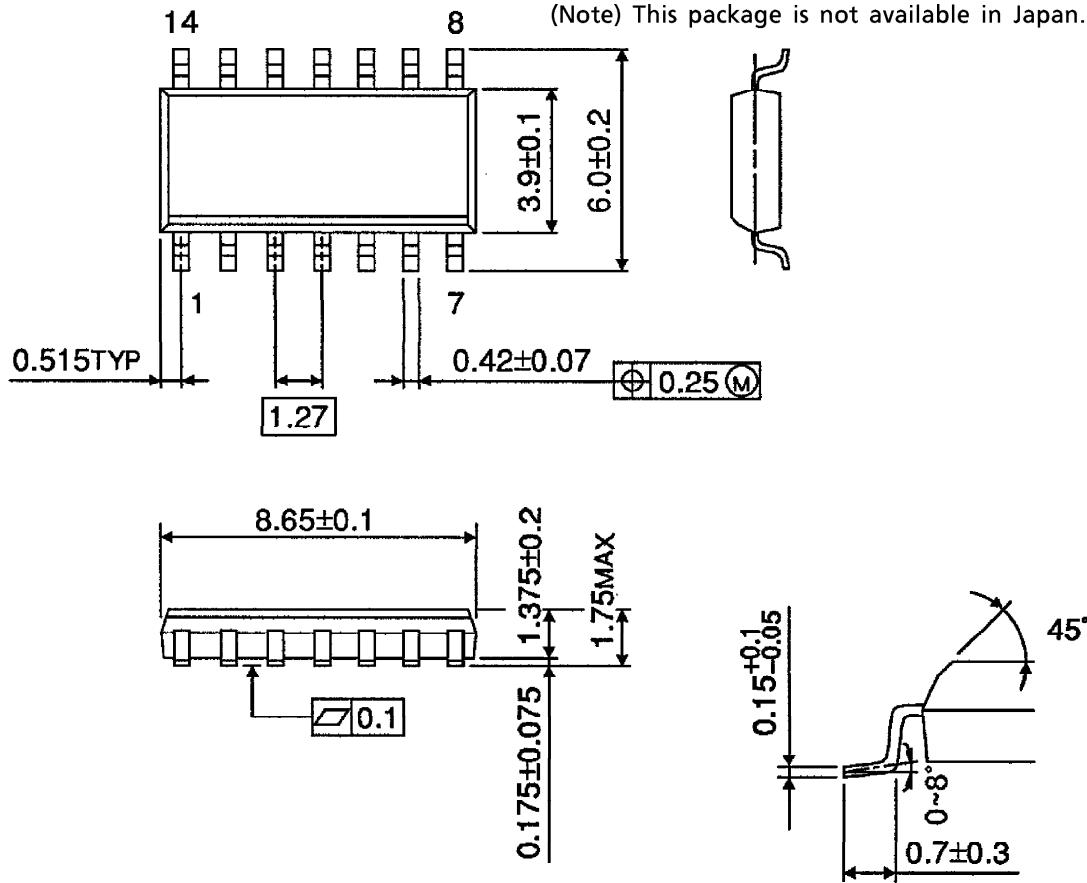
Unit : mm



Weight : 0.18g (Typ.)

**OUTLINE DRAWING**  
SOL14-P-150-1.27

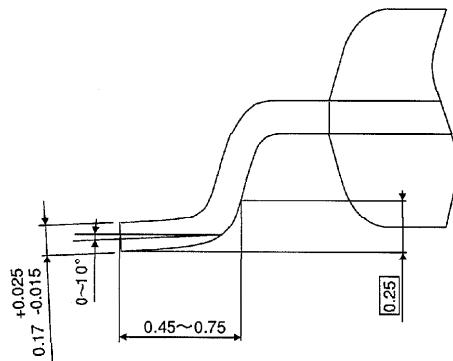
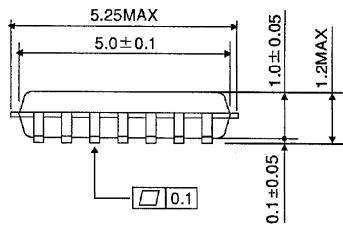
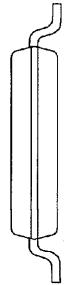
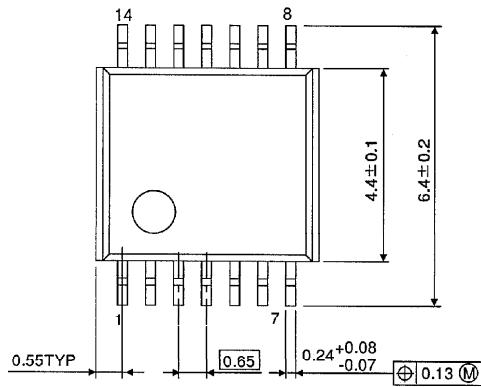
Unit : mm



Weight : 0.12g (Typ.)

**OUTLINE DRAWING**  
TSSOP14-P-0044-0.65

Unit : mm



Weight : 0.06g (Typ.)